

MOM STRUCTURE HAVING A COPPER/TANTALUM NITRIDE/ TANTALUM
PENTOXIDE STACKED STRUCTURE INCORPORATED THEREIN

Abstract

The present invention provides for an integrated circuit
5 metal-oxide-metal' ("MOM") capacitor that has a first
electrode, a tantalum pentoxide layer formed on the first
electrode, a first barrier layer formed on the tantalum
pentoxide layer, and a second copper electrode formed on the
first barrier layer. In one embodiment, the first barrier
10 layer of the MOM capacitor is tantalum nitride.

This Sheet Has Been Replaced

